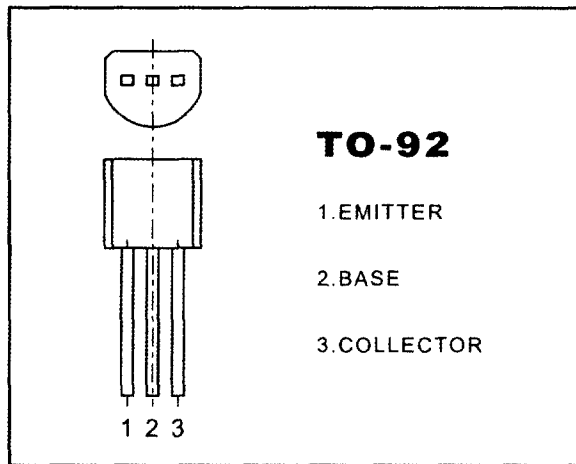


## TO-92 Plastic-Encapsulate Transistors

## A92 TRANSISTOR(PNP)



## FEATURES

## Power dissipation

 $P_{CM}: 0.625W$  ( $T_{amb}=25^{\circ}C$ )

## Collector current

 $I_{CM}: -0.5 A$ 

## Collector-base voltage

 $V_{(BR)CBO}: -300V$ 

## Operating and storage junction temperature range

 $T_J, T_{stg}: -55^{\circ}C$  to  $+150^{\circ}C$ 

## ELECTRICAL CHARACTERISTICS

 $(T_{amb}=25^{\circ}C$  unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100 \mu A, I_E = 0$	-300		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1 mA, I_B = 0$	-300		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10 \mu A, I_C = 0$	-5		V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -200 V, I_E = 0$		-0.25	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -3 V, I_C = 0$		-0.25	$\mu A$
DC current gain	$h_{FE(1)}$	$V_{CE} = -10 V, I_C = -1 mA$	25		
	$h_{FE(2)}$	$V_{CE} = -10 V, I_C = -10 mA$	80	250	
	$h_{FE(3)}$	$V_{CE} = -10 V, I_C = -50 mA$	25		
Collector-emitter saturation voltage	$V_{CEsat}$	$I_C = -20 mA, I_B = -2 mA$		-0.5	V
Base-emitter saturation voltage	$V_{BEsat}$	$I_C = -20 mA, I_B = -2 mA$		-0.9	V
Transition frequency	$f_T$	$V_{CE} = -5 V, I_C = -10 mA$ $f = 30 MHz$	50		MHz

CLASSIFICATION OF  $h_{FE(2)}$ 

Rank	A	B1	B2	C
Range	80-100	100-150	150-200	200-250

# Typical Characteristics

A92

